

2SK4072

Silicon N-channel MOSFET

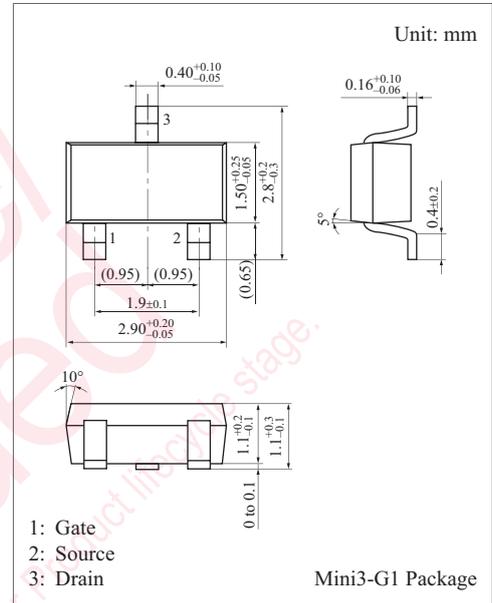
For switching circuits

■ Features

- High-speed switching
- Wide frequency band

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|--------------------------------|-----------|-------------|------------------|
| Drain-source surrender voltage | V_{DSS} | 50 | V |
| Gate-source surrender voltage | V_{GSS} | ± 7 | V |
| Drain current | I_D | 100 | mA |
| Peak drain current | I_{DP} | 200 | mA |
| Power dissipation | P_D | 200 | mW |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |



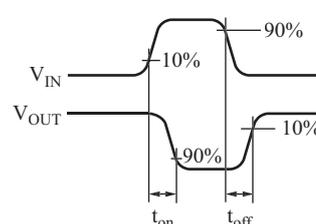
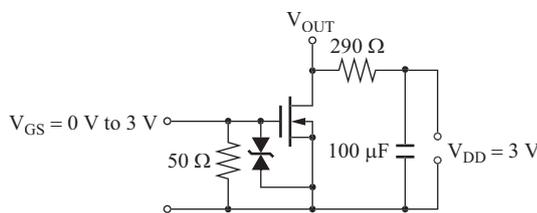
Marking Symbol: 5F

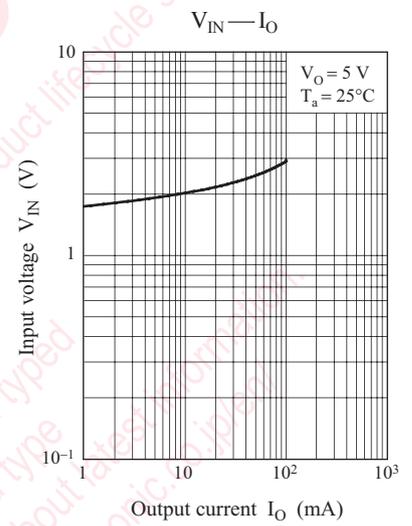
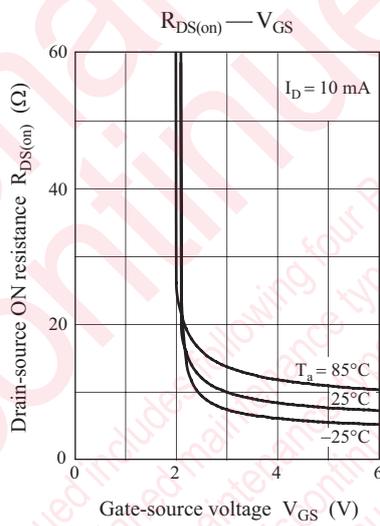
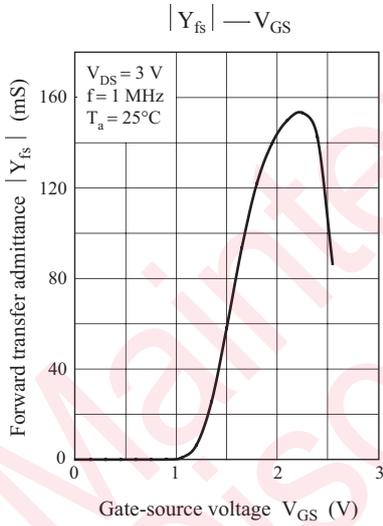
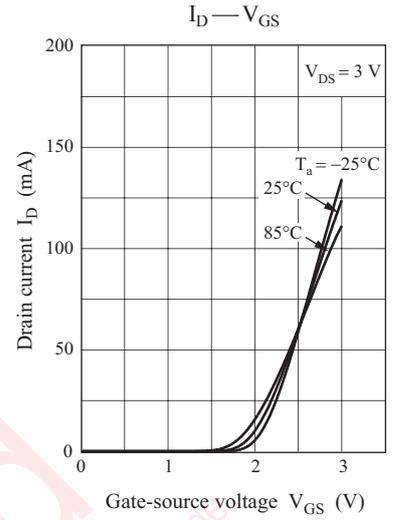
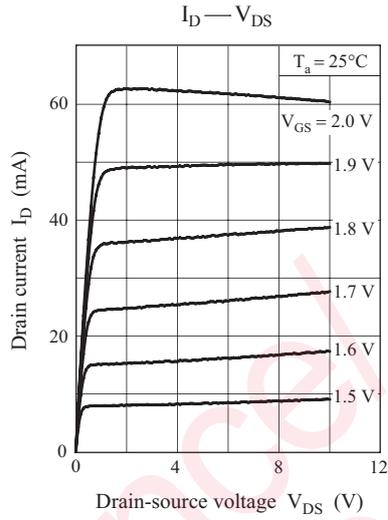
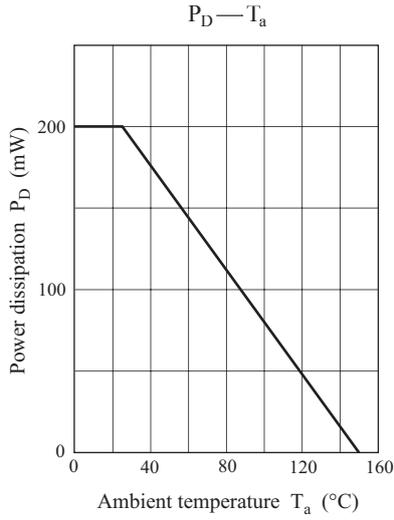
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|--------------|--|-----|-----|---------|---------------|
| Drain-source surrender voltage | V_{DSS} | $I_D = 10 \mu\text{A}, V_{GS} = 0$ | 50 | | | V |
| Drain-source cutoff current | I_{DSS} | $V_{DS} = 50 \text{ V}, V_{GS} = 0$ | | | 1.0 | μA |
| Gate-source cutoff current | I_{GSS} | $V_{GS} = \pm 7 \text{ V}, V_{DS} = 0$ | | | ± 5 | μA |
| Gate threshold voltage | V_{TH} | $I_D = 1.0 \mu\text{A}, V_{DS} = 3.0 \text{ V}$ | 0.9 | 1.2 | 1.5 | V |
| Drain-source ON resistance | $R_{DS(on)}$ | $I_D = 10 \text{ mA}, V_{GS} = 4.0 \text{ V}$ | | 6 | 12 | Ω |
| | | $I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ | | 8 | 15 | |
| Forward transfer admittance | $ Y_{fs} $ | $I_D = 10 \text{ mA}, V_{DS} = 3.0 \text{ V}$ | 20 | 60 | | mS |
| Short-circuit forward transfer capacitance (Common source) | C_{iss} | $V_{DS} = 3 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$ | | 12 | | pF |
| Short-circuit output capacitance (Common source) | C_{oss} | | | 7 | | pF |
| Reverse transfer capacitance (Common source) | C_{rss} | | | 3 | | pF |
| Turn-on time * | t_{on} | $V_{DD} = 3 \text{ V}, V_{GS} = 0 \text{ V to } 3 \text{ V}, R_L = 470 \Omega$ | | 200 | | ns |
| Turn-off time * | t_{off} | $V_{DD} = 3 \text{ V}, V_{GS} = 3 \text{ V to } 0 \text{ V}, R_L = 470 \Omega$ | | 200 | | ns |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: t_{on}, t_{off} measurement circuit





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